

The claims have been amended to read as follows:

1. (Amended) A semiconductor structure formed in a semiconductor material of a first conductivity type, the semiconductor material having a first dopant concentration, the semiconductor structure comprising:

a first region of the first conductivity type formed in the semiconductor material, the first region having a dopant concentration that is greater than the dopant concentration of the semiconductor material;

a second region of a second conductivity type formed in the semiconductor material to adjoin the first region;

a layer of isolation material formed on the semiconductor material;

a conductive contact formed through the layer of isolation material to make an electrical contact with the first region;

a first metal trace formed over the layer of isolation material and the conductive contact;

a layer of insulation material formed on the first metal trace;

a conductive via formed through the layer of insulation material to make an electrical contact with the first metal trace;

a second metal trace formed on the layer of insulation material and the conductive via to make an electrical contact with the conductive via;

a layer of passivation material formed over the second metal trace, the layer of passivation material including nitride; and

a single titanium protection layer formed over the layer of isolation material and the conductive contact, and below the layer of passivation material.

10
7. (Amended) A semiconductor structure formed in a semiconductor material of a first conductivity type, the semiconductor material having a first dopant concentration, the semiconductor structure comprising:

a first region of the first conductivity type formed in the semiconductor material, the first region having a dopant concentration that is greater than the dopant concentration of the semiconductor material;

a second region of a second conductivity type formed in the semiconductor material to adjoin the first region;

a layer of isolation material formed on the semiconductor material;

A2
cmv
a conductive contact formed through the layer of isolation material to make an electrical contact with the first region;

a first metal trace formed over the layer of isolation material and the conductive contact;

a layer of insulation material formed on the first metal trace;

a conductive via formed through the layer of insulation material to make an electrical contact with the first metal trace;

a second metal trace formed on the layer of insulation material and the conductive via to make an electrical contact with the conductive via;

a layer of passivation material formed over the second metal trace, the layer of passivation material including nitride; and

a titanium protection layer formed over the layer of isolation material and the conductive contact, and below the layer of passivation material, the titanium protection layer being formed on and over the first metal trace.

13. (Amended) A semiconductor structure formed in a semiconductor material of a first conductivity type, the semiconductor material having a first dopant concentration, the semiconductor structure comprising:

A
a first region of the first conductivity type formed in the semiconductor material, the first region having a dopant concentration that is greater than the dopant concentration of the semiconductor material;

a second region of a second conductivity type formed in the semiconductor material to adjoin the first region;

AA
cmd.

- a layer of isolation material formed on the semiconductor material;
- a conductive contact formed through the layer of isolation material to make an electrical contact with the first region;
- a first metal trace formed over the layer of isolation material and the conductive contact;
- a layer of insulation material formed on the first metal trace;
- a conductive via formed through the layer of insulation material to make an electrical contact with the first metal trace;
- a second metal trace formed on the layer of insulation material and the conductive via to make an electrical contact with the conductive via;
- a layer of passivation material formed over the second metal trace, the layer of passivation material including nitride; and
- a titanium protection layer formed over the layer of isolation material and the conductive contact, and below the layer of passivation material, the titanium protection layer being formed on and over the second metal trace.
